A TSV Barrier Layer Polishing Slurry

Abstract:
The present invention relates to a TSV barrier layer chemical mechanical polishing slurry, including abrasives, combination metal corrosion inhibitors, chelating agents, oxidizing agents, silicon nitride inhibitors and pH regulators. The present polishing slurry has a higher SiO_2 removal rate of and a lower Si_3N_4 removal rate, which exhibits desirable planarization efficiency for the barrier layer and stops in the Si_3N_4 layer to form TSV. Furthermore, a desired correction of the defections of previous processes and polishing processes is achieved without contaminants.

No Suitable Figure